

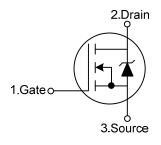
UTD20N03 Power MOSFET

# N-CHANNEL ENHANCEMENT MODE POWER M OSFET

# **■** FEATURES

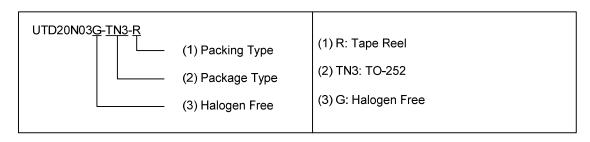
- \* Ambient operating temperature: 175°C
- \* Low drain-source and low on-resistance
- \* Logic level
- \* Perfect gate charge × R<sub>DS(ON)</sub> product
- \* Superior thermal resistance
- \* Avalanche rated
- \* Specified dv/dt
- \* For fast switching buck converters
- \* Halogen free

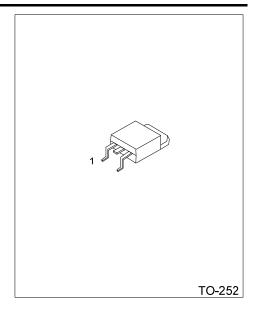
#### ■ SYMBOL



## ■ ORDERING INFORMATION

Ordering Number	Package	Pin Assignment			Dacking	
		1	2	3	Packing	
UTD20N03G-TN3-R	TO-252	G	D	S	Tape Reel	





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## ■ ABSOLUTE MAXIMUM RATINGS (T<sub>J</sub> = 25°C, unless otherwise specified))

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V <sub>DSS</sub>	30	V
Gate-Source Voltage		$V_{GS}$	±20	V
Continuous Drain Current (T <sub>C</sub> =25°C)		I <sub>D</sub>	30	Α
Pulsed Drain Current (T <sub>C</sub> =25°C)		$I_{DM}$	120	Α
IAValanche Energy	Single Pulsed (Note 2)	E <sub>AS</sub>	15	mJ
	Repetitive (Note 3)	E <sub>AR</sub>	6	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	6	kV/μs
Power Dissipation (T <sub>C</sub> =25°C)		$P_D$	60	W
Junction Temperature		TJ	+175	°C
Storage Temperature		T <sub>STG</sub>	-55 ~ +175	°C

- Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged Absolute maximum ratings are stress ratings only and functional device operation is not implied.
  - 2.  $I_D$  =15 A,  $V_{DD}$  =25 V,  $R_{GS}$  =25  $\Omega$
  - 3. Repetitive Rating: Pulse width limited by T<sub>J</sub>
  - 4.  $I_S = 30 \text{ A}$ ,  $V_{DS} = 24 \text{ V}$ ,  $di/dt = 100 \text{A}/\mu \text{s}$ ,  $T_{J(MAX)} = 175 \, ^{\circ}\text{C}$

#### **■ THERMAL DATA**

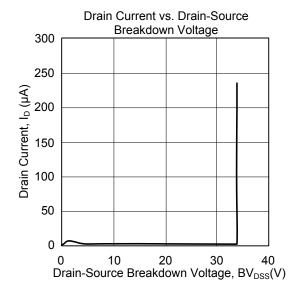
PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
Junction to Ambient	$\theta_{JA}$			100	°C/W
Junction to Case	$\theta_{JC}$		1.7	2.5	°C/W

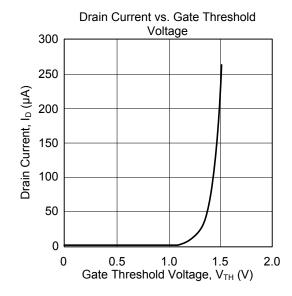
# ■ ELECTRICAL CHARACTERISTICS (T<sub>J</sub> =25°C, unless otherwise specified)

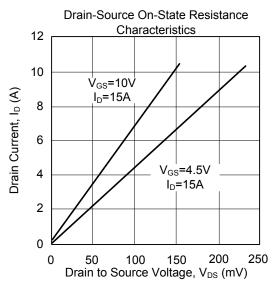
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT		
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0 V, I <sub>D</sub> =1 mA				V		
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =30 V,V <sub>GS</sub> =0 V		0.01	1	μΑ		
Gate-Source Leakage Current	$I_{GSS}$	V <sub>GS</sub> =20 V, V <sub>DS</sub> =0 V		1	100	nA		
ON CHARACTERISTICS								
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}$ , $I_D = 25\mu A$	1.2	1.6	2	V		
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	$V_{GS}$ =4.5 V, $I_{D}$ =15 A		22.9	31	mΩ		
Drain-Source On-State Resistance		V <sub>GS</sub> =10 V, I <sub>D</sub> =15 A		15.5	20	mΩ		
DYNAMIC PARAMETERS								
Input Capacitance	C <sub>ISS</sub>			530	700	pF		
Output Capacitance	Coss	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{MHz}$		200	275	pF		
Reverse Transfer Capacitance	$C_{RSS}$			60	90	pF		
Gate Resistance	$R_G$			1.3		Ω		
SWITCHING PARAMETERS								
Turn-ON Delay Time	$t_{D(ON)}$			6.2	9.3	ns		
Turn-ON Rise Time	t <sub>R</sub>	V <sub>DD</sub> =15 V, V <sub>GS</sub> =10 V,		11	17	ns		
Turn-OFF Delay Time	t <sub>D(OFF)</sub>	$I_D = 15 \text{ A}, R_G = 12.7 \Omega$		23	34	ns		
Turn-OFF Fall-Time	t <sub>F</sub>			18	27	ns		
Total Gate Charge	$Q_G$	$V_{DD} = 15 \text{ V}, I_D = 15 \text{ A}, V_{GS} = 5 \text{ V}$		8.4	11	nC		
Gate Source Charge	$Q_GS$	\\ -45\\ I -45 A		2.5	3.1	nC		
Gate Drain Charge	$Q_GD$	$V_{DD} = 15 \text{ V}, I_{D} = 15 \text{ A}$		6.4	9.6	nC		
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS								
Inverse Diode Forward Voltage	$V_{SD}$	I <sub>F</sub> =30 A, V <sub>GS</sub> =0 V		1.1	1.4	V		
Maximum Continuous Drain-Source Diode	ı				30	Α		
Forward Current	I <sub>S</sub>	T <sub>C</sub> =25°C			30	А		
Maximum Pulsed Drain-Source Diode	I <sub>SM</sub>	10-25 0			120	Α		
Forward Current	ISM					^		
Reverse Recovery Time	t <sub>RR</sub>	$V_R = 15 V_1 I_F = I_S$ , dl/dt = 100A/ $\mu$ s		15	18	ns		
Reverse Recovery Charge	$Q_{RR}$	νς 10 ν, 15 – 15, απαί – 100/ν μ5		2	3	nC		

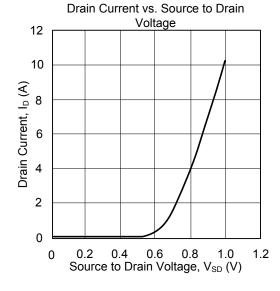
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#### ■ TYPICAL CHARACTERISTICS









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